

## **ABSTRACT OF THE DISCLOSURE**

The present invention discloses a ferroelectric register and a method for manufacturing a capacitor of the same. The ferroelectric register is configured to reduce probability of data storage failure due to a weak state capacitor, by connecting a plurality of capacitors in parallel in a ferroelectric capacitor unit for storing data, instead of using a single capacitor, thereby improving storage reliability and stability. In addition, the ferroelectric register obtains a data sensing margin by pumping a cell plate signal into not a power voltage level but a pumping voltage level.